

isc Silicon PNP Power Transistor

BD744

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -45V(\text{Min})$
- Collector Power Dissipation-
: $P_C = 90W @ I_C = 25^\circ C$
- 15A Continuous Collector Current
- Complement to Type BD743
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

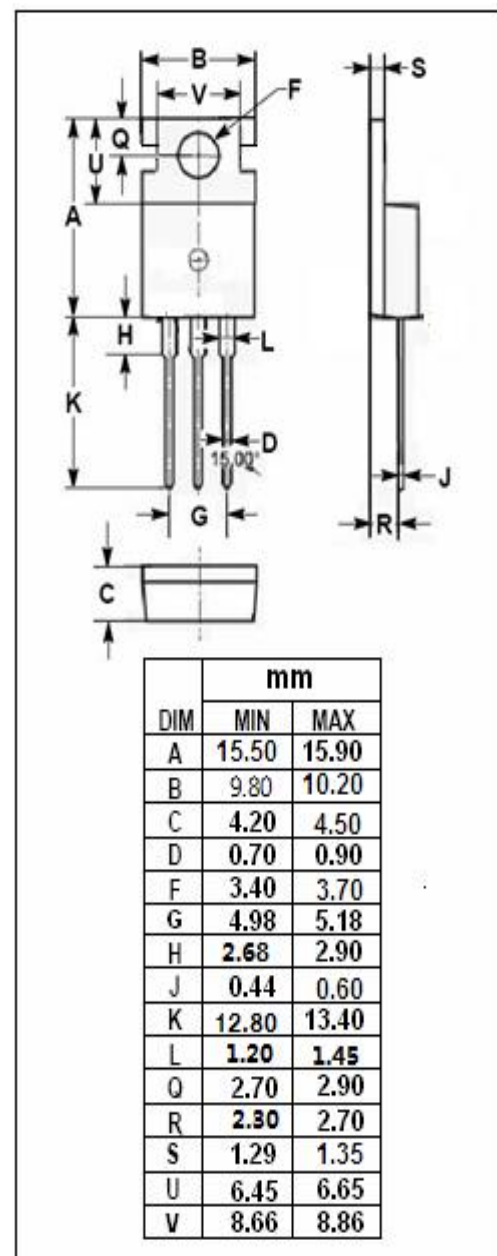
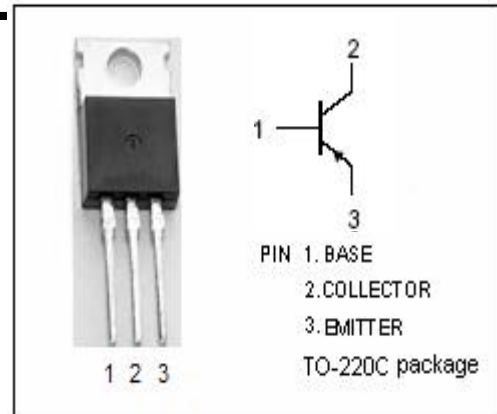
- Designed for use in general purpose power amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_{CM}	Collector Current-Peak	-20	A
I_B	Base Current-Continuous	-5	A
P_C	Collector Power Dissipation @ $T_a = 25^\circ C$	2	W
	Collector Power Dissipation @ $T_C = 25^\circ C$	90	
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.4	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ C/W$



isc Silicon PNP Power Transistor**BD744****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN		MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA; I _B = 0	-45			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = -5A; I _B = -0.5A			-1.0	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = -15A; I _B = -5A			-3.0	V
V _{BE(on)-1}	Base-Emitter On Voltage	I _C = -5A; V _{CE} = -4V			-1.0	V
V _{BE(on)-2}	Base-Emitter On Voltage	I _C = -15A; V _{CE} = -4V			-3.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -50V; I _E = 0			-0.1	mA
		V _{CB} = -50V; I _E = 0; T _C = 125°C			-5.0	
I _{CEO}	Collector Cutoff Current	V _{CE} = -30V; I _B = 0			-0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-0.5	mA
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -4V	40			
h _{FE-2}	DC Current Gain	I _C = -5A; V _{CE} = -4V	20		150	
h _{FE-3}	DC Current Gain	I _C = -15A; V _{CE} = -4V	5			

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